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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/563,854	06/09/2006	Euijoon Yoon	20506/0203830-US0	3828
7278 DARBY & DA	7590 10/28/200 RBY P.C.	EXAMINER		
P.O. BOX 770	4-4:	MALDONADO, JULIO J		
Church Street S New York, NY		ART UNIT	PAPER NUMBER	
			2823	
			MAIL DATE	DELIVERY MODE
			10/28/2008	PAPER

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

Advisory Action Before the Filing of an Appeal Brief

Application No.	Applicant(s)	
10/563,854	YOON ET AL.	
Examiner	Art Unit	
JULIO J. MALDONADO	2823	

	JULIO J. MALDONADO	2823	
The MAILING DATE of this communication appe	ars on the cover sheet with the	correspondence add	ress
THE REPLY FILED <u>08 October 2008</u> FAILS TO PLACE THIS A		-	
1. The reply was filed after a final rejection, but prior to or on application, applicant must timely file one of the following application in condition for allowance; (2) a Notice of Apperfor Continued Examination (RCE) in compliance with 37 C periods:	the same day as filing a Notice of replies: (1) an amendment, affidavi eal (with appeal fee) in compliance	Appeal. To avoid abar t, or other evidence, w with 37 CFR 41.31; or	hich places the (3) a Request
a) The period for reply expires <u>3</u> months from the mailing date	of the final rejection.		
b) The period for reply expires on: (1) the mailing date of this A no event, however, will the statutory period for reply expire to Examiner Note: If box 1 is checked, check either box (a) or (MONTHS OF THE FINAL REJECTION. See MPEP 706.07(f)	ater than SIX MONTHS from the mailing b). ONLY CHECK BOX (b) WHEN THE c).	g date of the final rejection FIRST REPLY WAS FII	n. LED WITHIN TWO
Extensions of time may be obtained under 37 CFR 1.136(a). The date of have been filed is the date for purposes of determining the period of extunder 37 CFR 1.17(a) is calculated from: (1) the expiration date of the set forth in (b) above, if checked. Any reply received by the Office later may reduce any earned patent term adjustment. See 37 CFR 1.704(b). NOTICE OF APPEAL	ension and the corresponding amount hortened statutory period for reply origi	of the fee. The appropria nally set in the final Offic	ate extension fee e action; or (2) as
 The Notice of Appeal was filed on A brief in comp filing the Notice of Appeal (37 CFR 41.37(a)), or any exter Notice of Appeal has been filed, any reply must be filed wind AMENDMENTS 	nsion thereof (37 CFR 41.37(e)), to	avoid dismissal of the	
	and prior to the data of filing a bring	مطالم مسلم مسلم مسلم النبيد	
3. The proposed amendment(s) filed after a final rejection, be (a) They raise new issues that would require further cor (b) They raise the issue of new matter (see NOTE below (c) They are not deemed to place the application in beta appeal; and/or	nsideration and/or search (see NO w);	ΓE below);	
(d) They present additional claims without canceling a converse NOTE: (See 37 CFR 1.116 and 41.33(a)).	corresponding number of finally reje	ected claims.	
4. The amendments are not in compliance with 37 CFR 1.12 5. Applicant's reply has overcome the following rejection(s):		mpliant Amendment (l	PTOL-324).
6. Newly proposed or amended claim(s) would be all non-allowable claim(s).		timely filed amendmer	t canceling the
7. For purposes of appeal, the proposed amendment(s): a) [how the new or amended claims would be rejected is prov The status of the claim(s) is (or will be) as follows: Claim(s) allowed:		l be entered and an e.	xplanation of
Claim(s) objected to: <u>13 and 14</u> . Claim(s) rejected: <u>1-12 and 15-19</u> . Claim(s) withdrawn from consideration: AFFIDAVIT OR OTHER EVIDENCE			
 The affidavit or other evidence filed after a final action, but because applicant failed to provide a showing of good and was not earlier presented. See 37 CFR 1.116(e). 			
9. The affidavit or other evidence filed after the date of filing entered because the affidavit or other evidence failed to of showing a good and sufficient reasons why it is necessary	vercome <u>all</u> rejections under appear and was not earlier presented. Se	al and/or appellant fail ee 37 CFR 41.33(d)(1	s to provide a
10.	n of the status of the claims after e	ntry is below or attach	ed.
 The request for reconsideration has been considered but See Continuation Sheet. 	t does NOT place the application in	condition for allowan	ce because:
12. ☐ Note the attached Information <i>Disclosure Statement</i>(s). (13. ☐ Other:	PTO/SB/08) Paper No(s)		
	/George Fourson/ Primary Examiner, Art U	nit 2823	

Continuation of 11. does NOT place the application in condition for allowance because: Applicant's arguments filed 10/08/2008 have been fully considered but they are not persuasive.

Applicants argue, "...Claims 1, 15 and 16 are rejected under 35 U.S.C. § 112, first paragraph for failing to comply with the written description requirement. Applicants respectfully traverse the rejection. Support for "collectively increasing" the semiconductor layers can be found in the Specification. For example, the Specification, page 6, lines 6-9, discloses "[i]n a preferred embodiment, the nitride semiconductor epitaxial layer 110 is GaN that is formed by two steps of growing a low-temperature buffer layer and growing a high-temperature layer on the low-temperature buffer layer." To grow a high-temperature layer on the low-temperature layer requires at least collectively increasing the temperature of these layers. This growth method was described in U.S. Patent No. 5, 290,393, which is disclosed in the Specification at page 1, lines 19-23...As to the growth of a third nitride semiconductor epitaxial layer 130, the Specification, at pages 6, line 22 bridging through page 7, line 1, discloses that "a nitride semiconductor epitaxial layer 130 is grown on the nitride semiconductor epitaxial layer 120." Accordingly, the Specification provides support for the features of pending claims 1, 15 and 16...".

In response to the applicants' argument, claims 1, 15 and 16 as amended in the reply filed on 03/28/2008 recites a step of releasing nitrogen from a second nitride layer (claims 1 and 16), or converting a nitride layer into a metal layer (claim 15) by collectively increasing a temperature of a first, second and third nitride layers. The support argued by the applicants is for a deposition temperature, which is at a different stage of the manufacturing process, not during the decomposition of said second nitride layer. Furthermore, the disclosed specification teaches wherein the second and the third semiconductor layers are formed at a temperature of 300oC to 800oC (page 6, line 21 - page 7, line 11), and, after forming said nitride layers, a temperature is raised to 900oC or more to decompose said second nitride layer (page 8, lines 12 - 18). There is no support to any specific heating that would render the claim language in claims 1, 15 and 16 inherent. Also, although it is inherent that the decomposing of the second nitride layer will heat the first and third nitride layer, there is no support in the specification for the claim language in claims 1, 15 and 16. Therefore, the rejection of claims 1, 15 and 16 is not withdrawn in view of the applicants' arguments.